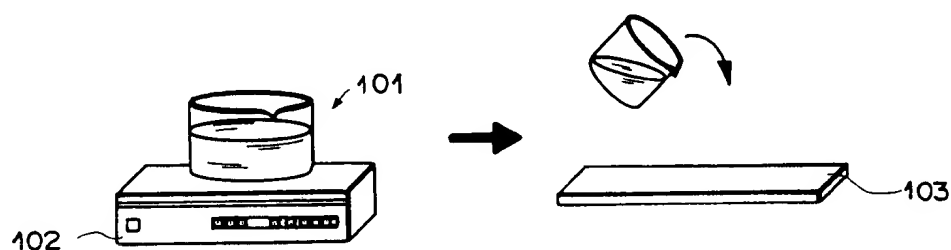




F I G . 1



0977636 000004
F07030 000004

F I G . 2

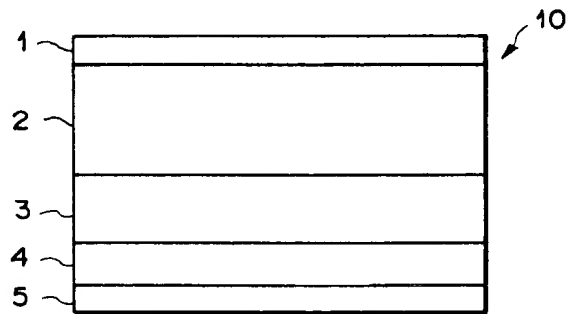
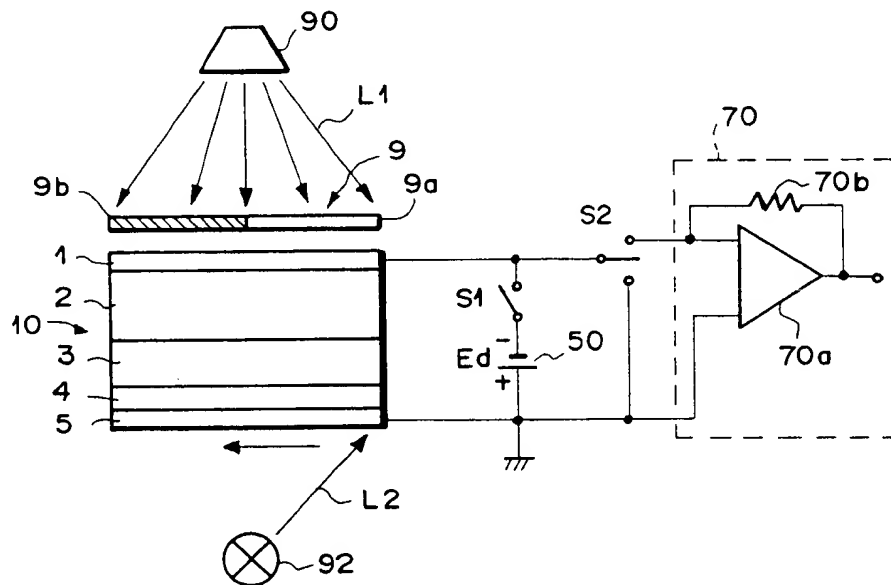
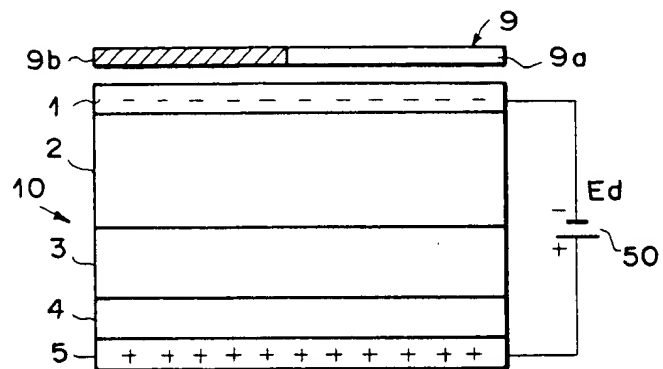


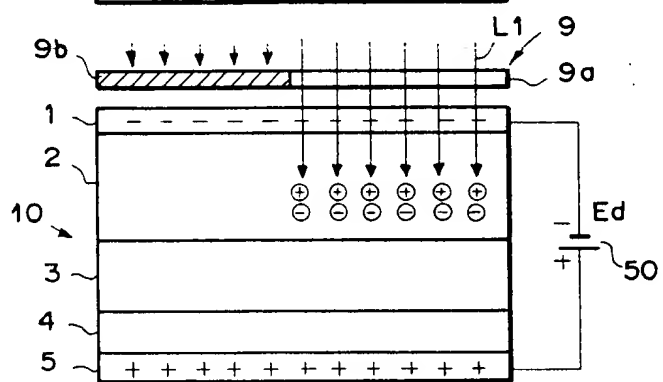
FIG. 3



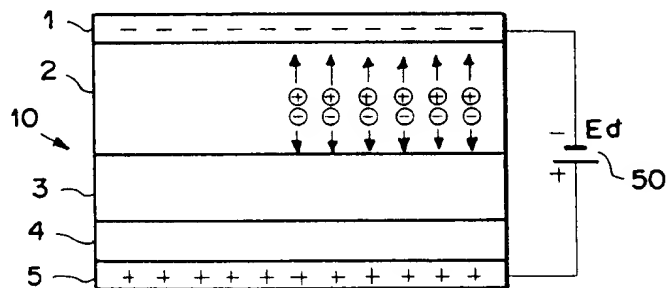
F I G . 4 A



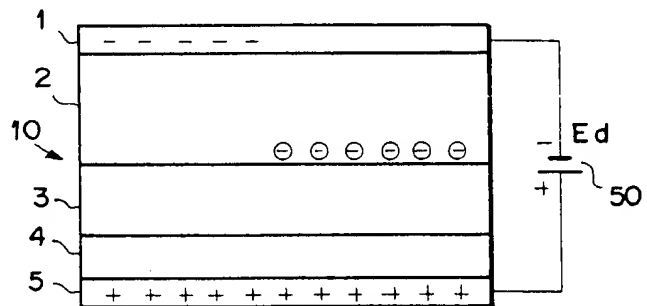
F I G . 4 B



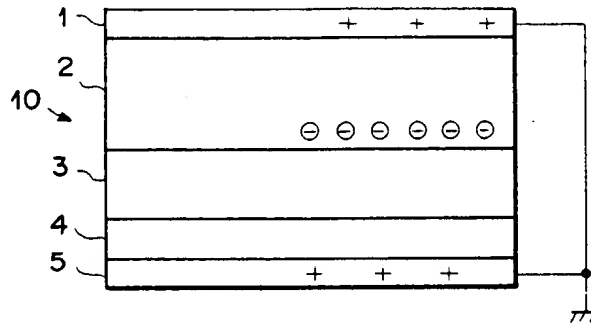
F I G . 4 C



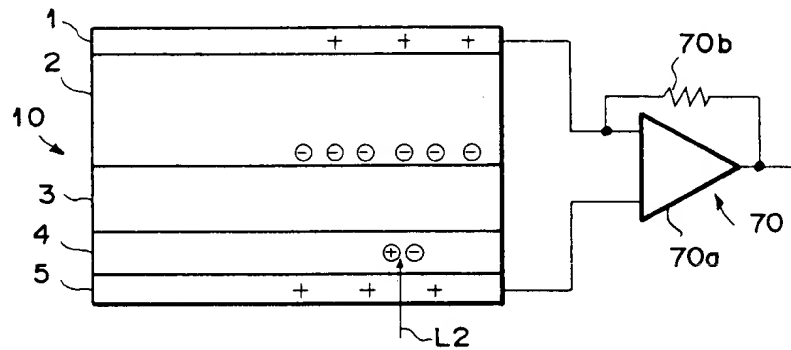
F I G . 4 D



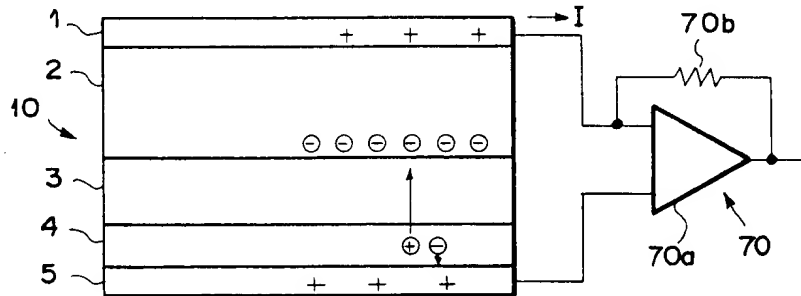
F I G. 5A



F I G. 5B



F I G. 5C



F I G. 5D

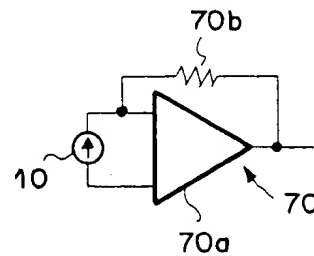
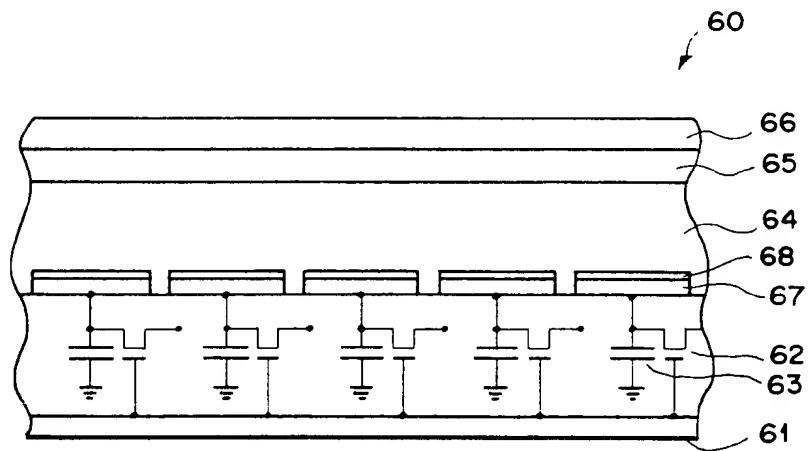
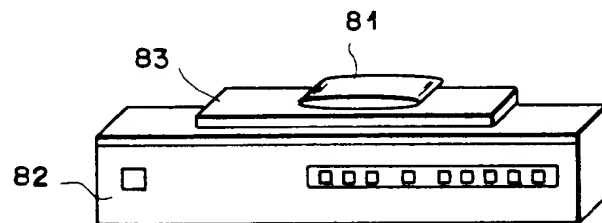


FIG. 6



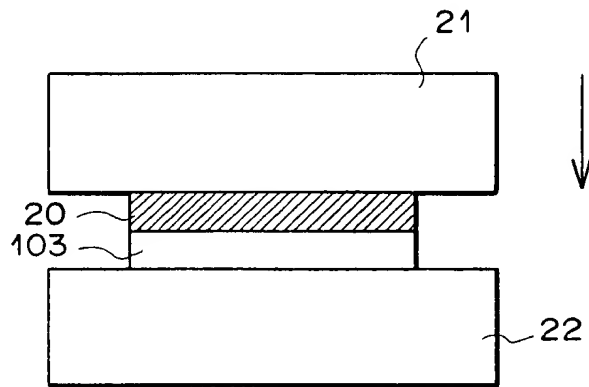
A cross-sectional view of a semiconductor device 60. The device consists of a substrate with a series of five transistors connected in series. Each transistor has a gate electrode, a source, and a drain. The gates are connected to a common input line, and the sources are connected to ground. The drains are connected to a common output line 76. The output line 76 is connected to an inverter 75, which is also connected to ground.

F I G . 8



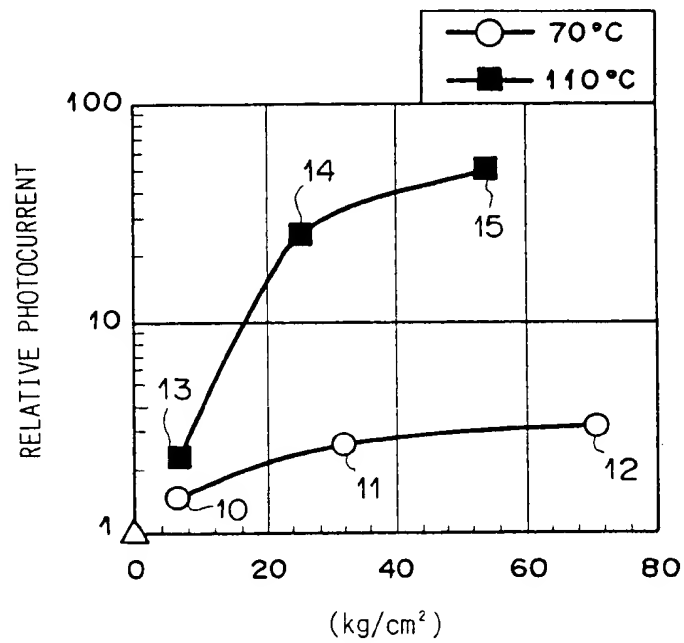
PRIOR ART

FIG. 9

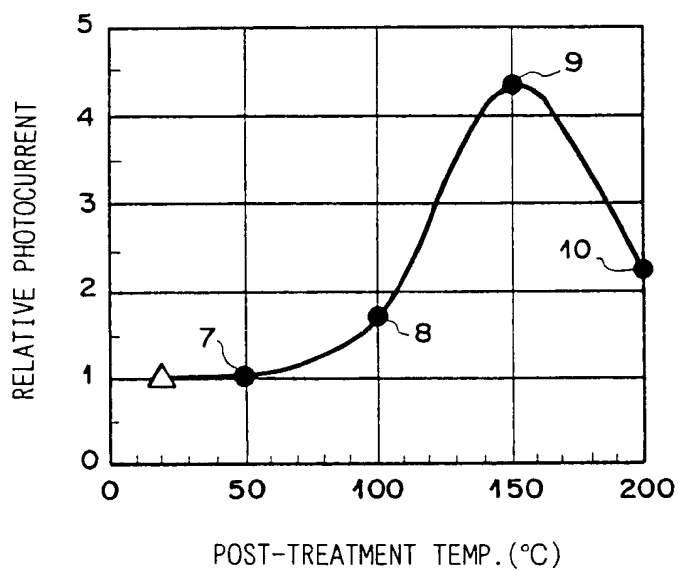


202-293-7060 FAX

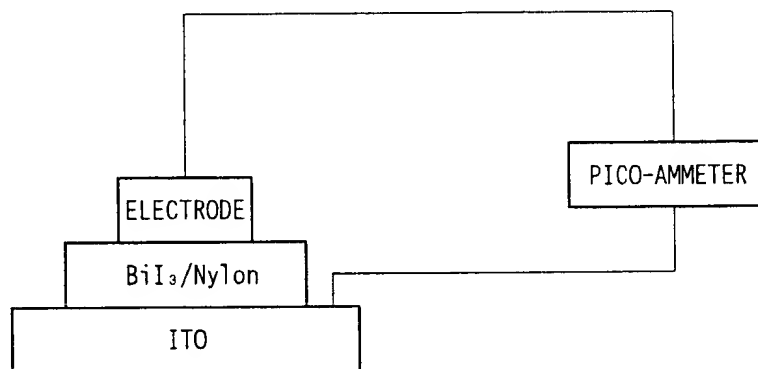
F I G . 10



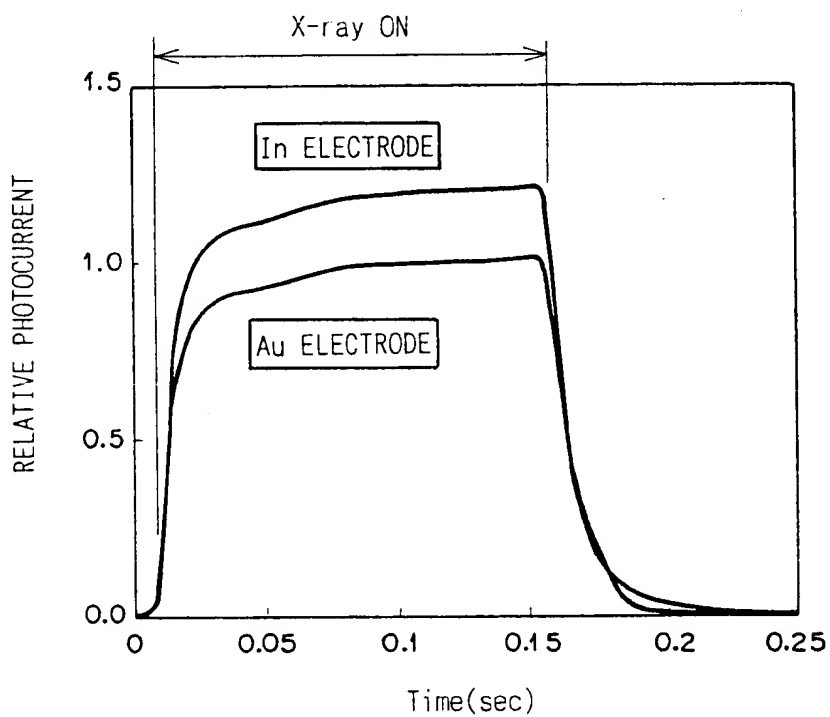
F I G . 1 1



F I G . 1 2



F I G . 13



202-293-7060